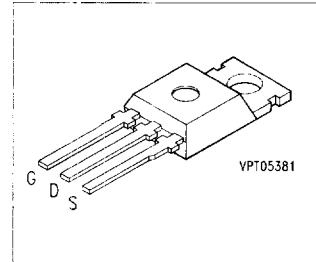


## SIPMOS® Power Transistor

## BUZ 70 L

- N channel
- Enhancement mode
- Avalanche-rated
- Logic Level



Type	$V_{DS}$	$I_D$	$R_{DS(on)}$	Package <sup>1)</sup>	Ordering Code
<b>BUZ 70 L</b>	60 V	12 A	0.15 $\Omega$	TO-220 AB	C67078-S1325-A2

### Maximum Ratings

Parameter	Symbol	Values	Unit
Continuous drain current, $T_C = 33\text{ }^\circ\text{C}$	$I_D$	<b>12</b>	A
Pulsed drain current, $T_C = 25\text{ }^\circ\text{C}$	$I_{D,puls}$	<b>48</b>	
Avalanche current, limited by $T_{j,max}$	$I_{AR}$	<b>12</b>	
Avalanche energy, periodic limited by $T_{j(max)}$	$E_{AR}$	<b>1</b>	mJ
Avalanche energy, single pulse $I_D = 12\text{ A}$ , $V_{DD} = 25\text{ V}$ , $R_{GS} = 25\text{ }\Omega$ $L = 48.6\text{ }\mu\text{H}$ , $T_j = 25\text{ }^\circ\text{C}$	$E_{AS}$	<b>6</b>	
Gate-source voltage	$V_{GS}$	<b><math>\pm 10</math></b>	V
Gate-source peak voltage aperiodic	$V_{gs}$	<b><math>\pm 20</math></b>	
Power dissipation, $T_C = 25\text{ }^\circ\text{C}$	$P_{tot}$	<b>40</b>	W
Operating and storage temperature range	$T_j, T_{stg}$	<b><math>-55 \dots +150</math></b>	$^\circ\text{C}$
Thermal resistance, chip-case	$R_{th,jc}$	<b><math>\leq 3.1</math></b>	K/W
DIN humidity category, DIN 40 040		<b>E</b>	–
IEC climatic category, DIN IEC 68-1		<b>55/150/56</b>	

1) See chapter Package Outlines.

**Electrical Characteristics**at  $T_j = 25\text{ °C}$ , unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

**Static characteristics**

Drain-source breakdown voltage $V_{GS} = 0\text{ V}$ , $I_D = 0.25\text{ mA}$	$V_{(BR)DSS}$	60	–	–	V
Gate threshold voltage $V_{GS} = V_{DS}$ , $I_D = 1\text{ mA}$	$V_{GS(th)}$	1.5	2.0	2.5	
Zero gate voltage drain current $V_{DS} = 60\text{ V}$ , $V_{GS} = 0\text{ V}$ $T_j = 25\text{ °C}$ $T_j = 125\text{ °C}$	$I_{DSS}$	–	0.1	1.0	$\mu\text{A}$
Gate-source leakage current $V_{GS} = 20\text{ V}$ , $V_{DS} = 0\text{ V}$	$I_{GSS}$	–	10	100	nA
Drain-source on-resistance $V_{GS} = 5\text{ V}$ , $I_D = 6.0\text{ A}$	$R_{DS(on)}$	–	0.12	0.15	$\Omega$

**Dynamic characteristics**

Forward transconductance $V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$ , $I_D = 6.0\text{ A}$	$g_{fs}$	2.0	7.5	–	S
Input capacitance $V_{GS} = 0\text{ V}$ , $V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$	$C_{iss}$	–	420	560	pF
Output capacitance $V_{GS} = 0\text{ V}$ , $V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$	$C_{oss}$	–	160	250	
Reverse transfer capacitance $V_{GS} = 0\text{ V}$ , $V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$	$C_{rss}$	–	60	110	
Turn-on time $t_{on}$ , ( $t_{on} = t_{d(on)} + t_r$ ) $V_{DD} = 30\text{ V}$ , $V_{GS} = 5\text{ V}$ , $I_D = 3\text{ A}$ , $R_{GS} = 50\text{ }\Omega$	$t_{d(on)}$	–	15	25	ns
	$t_r$	–	55	80	
Turn-off time $t_{off}$ , ( $t_{off} = t_{d(off)} + t_f$ ) $V_{DD} = 30\text{ V}$ , $V_{GS} = 5\text{ V}$ , $I_D = 3\text{ A}$ , $R_{GS} = 50\text{ }\Omega$	$t_{d(off)}$	–	45	60	
	$t_f$	–	40	55	

### Electrical Characteristics (cont'd)

at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified.

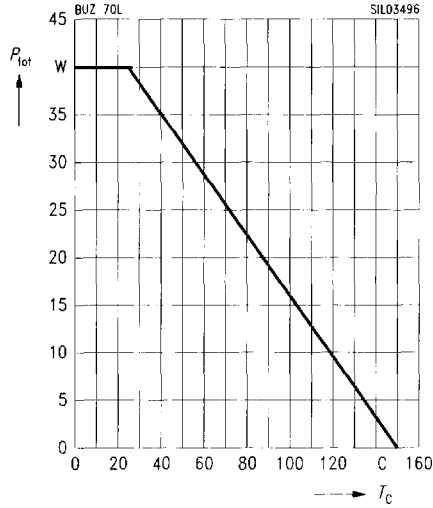
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
<b>Reverse diode</b>					
Continuous reverse drain current $T_C = 25\text{ }^\circ\text{C}$	$I_S$	–	–	12	A
Pulsed reverse drain current $T_C = 25\text{ }^\circ\text{C}$	$I_{SM}$	–	–	48	
Diode forward on-voltage $I_S = 24\text{ A}$ , $V_{GS} = 0\text{ V}$	$V_{SD}$	–	1.5	1.8	V
Reverse recovery time $V_R = 30\text{ V}$ , $I_F = I_S$ , $di_F / dt = 100\text{ A}/\mu\text{s}$	$t_{rr}$	–	60	–	ns
Reverse recovery charge $V_R = 30\text{ V}$ , $I_F = I_S$ , $di_F / dt = 100\text{ A}/\mu\text{s}$	$Q_{rr}$	–	0.10	–	$\mu\text{C}$



Characteristics at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified.

**Total power dissipation**

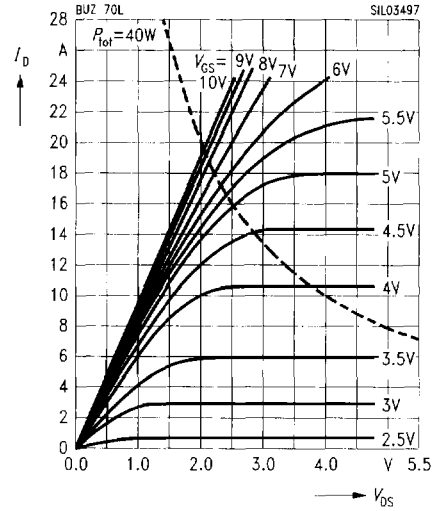
$P_{\text{tot}} = f(T_C)$



**Typ. output characteristics**

$I_D = f(V_{DS})$

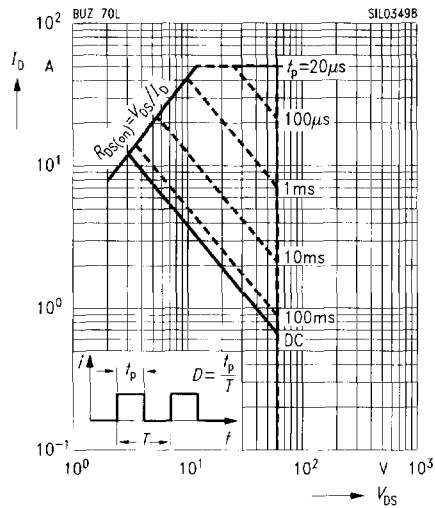
parameter:  $t_p = 80\text{ }\mu\text{s}$



**Safe operating area**

$I_D = f(V_{DS})$

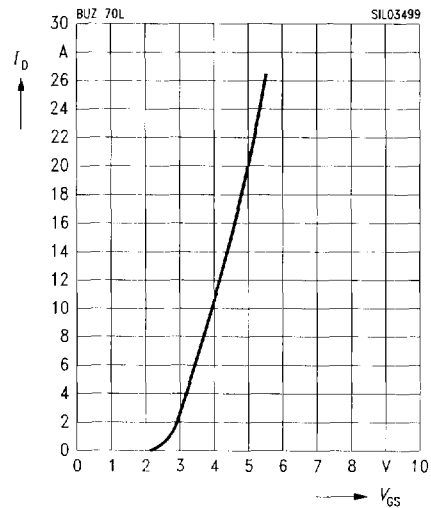
parameter:  $D = 0.01$ ,  $T_C = 25\text{ }^\circ\text{C}$



**Typ. transfer characteristics**

$I_D = f(V_{GS})$

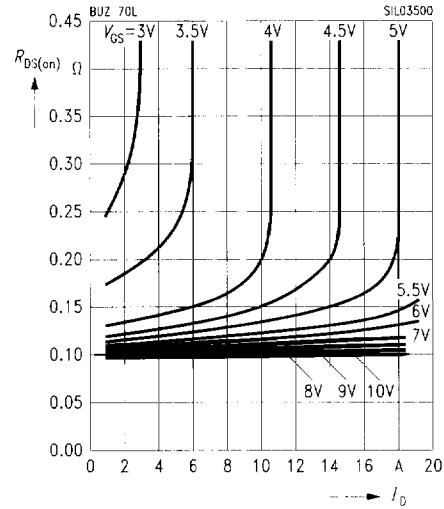
parameter:  $t_p = 80\text{ }\mu\text{s}$ ,  $V_{DS} = 25\text{ V}$



**Typ. drain-source on-resistance**

$R_{DS(on)} = f(I_D)$

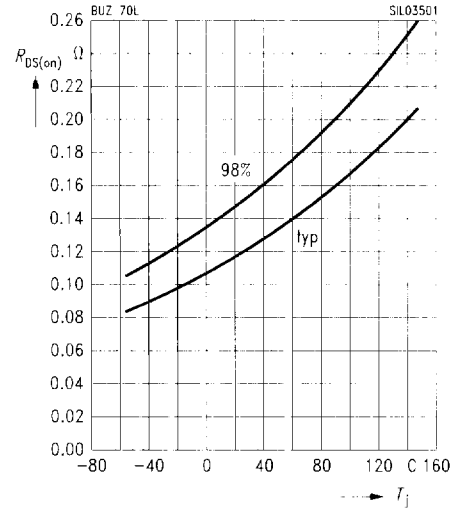
parameter:  $V_{GS}$



**Drain-source on-resistance**

$R_{DS(on)} = f(T_j)$

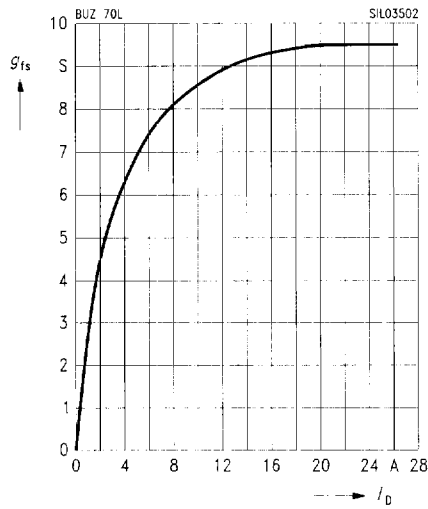
parameter:  $I_D = 6.0$  A,  $V_{GS} = 5$  V, (spread)



**Typ. forward transconductance**

$g_{fs} = f(I_D)$

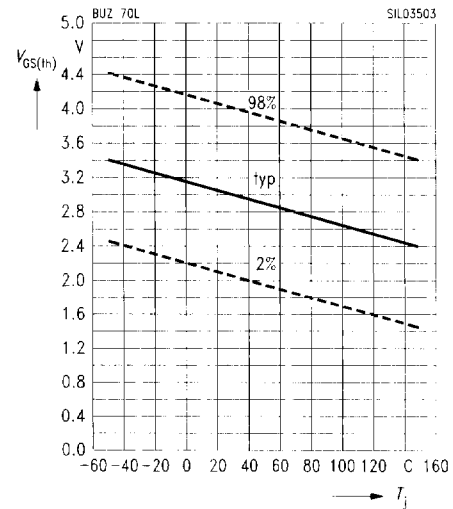
parameter:  $t_p = 80$   $\mu s$



**Gate threshold voltage**

$V_{GS(th)} = f(T_j)$

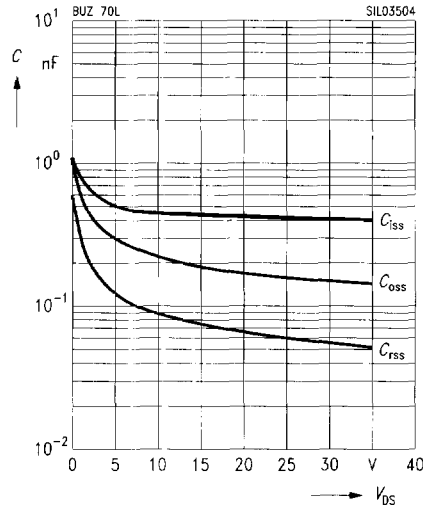
parameter:  $V_{GS} = V_{DS}$ ,  $I_D = 1$  mA, (spread)



**Typ. capacitances**

$C = f(V_{DS})$

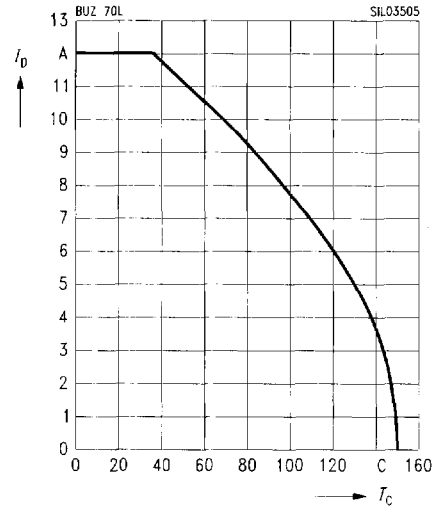
parameter:  $V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$



**Drain current**

$I_D = f(T_C)$

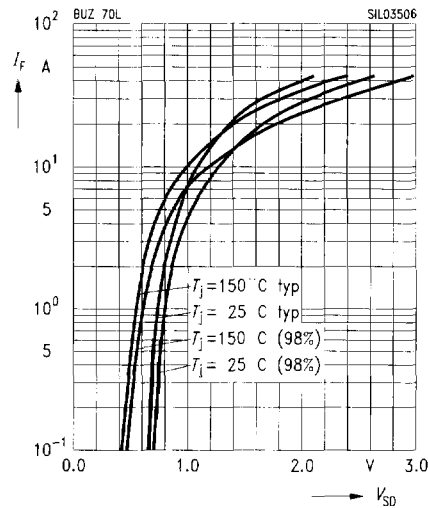
parameter:  $V_{GS} \geq 5 \text{ V}$



**Forward characteristics of reverse diode**

$I_F = f(V_{SD})$

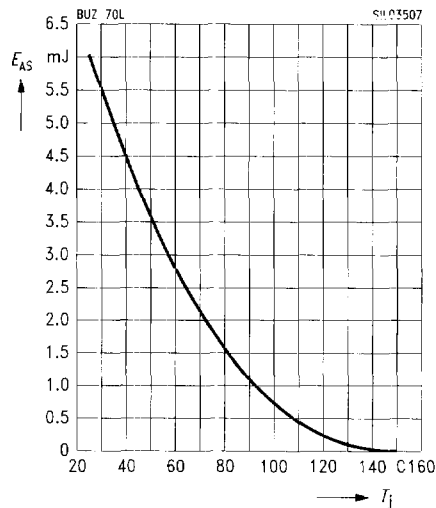
parameter:  $T_j, t_p = 80 \mu\text{s}, (\text{spread})$



**Avalanche energy  $E_{AS} = f(T_j)$**

parameter:  $I_D = 12 \text{ A}, V_{DD} = 25 \text{ V}$

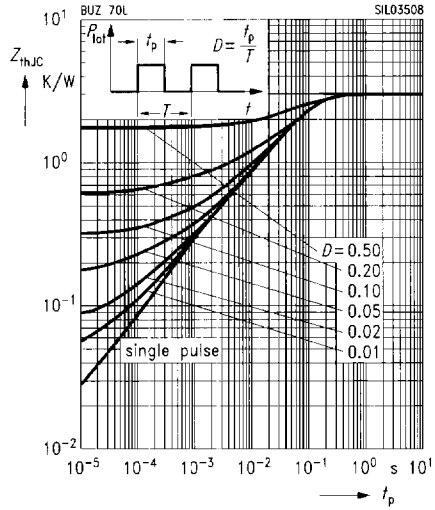
$R_{GS} = 25 \Omega, L = 48.6 \mu\text{H}$



**Transient thermal impedance**

$Z_{thJC} = f(t_p)$

parameter:  $D = t_p / T$



**Typ. gate charge**

$V_{GS} = f(Q_{Gate})$

parameter:  $I_{D,puls} = 18 A$

